

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-60V	48mΩ @ V _{GS} = -10V	-5.2A
	60mΩ @ V _{GS} = -4.5V	-4.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

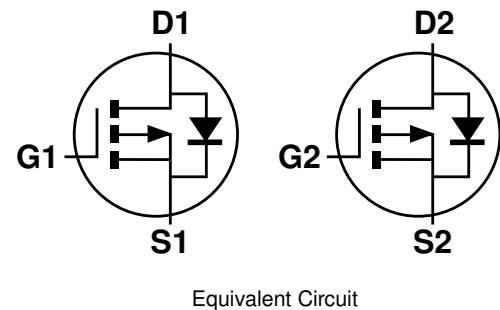
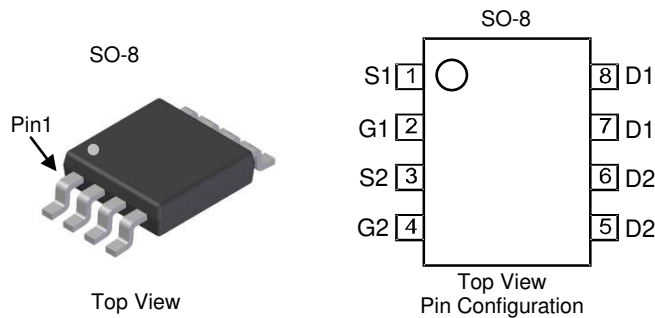
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C – ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching – ensures more reliable and robust end application
- Low R_{DS(ON)} – minimises power losses
- Low Q_g – minimises switching losses
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMPH6050SSDQ](#))**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.076 grams (Approximate)

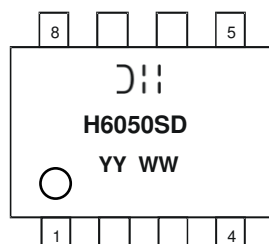


Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6050SSD-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 H6050SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	T _A = +25°C	-5.2	A
		T _A = +100°C	-3.7	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-35	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-2.0	A	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-25	A	
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	33	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	T _A = +25°C	103
		Steady state	
		t < 10s	64
Total Power Dissipation (Note 6)	P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	T _A = +25°C	75
		Steady state	
		t < 10s	47
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	13	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	µA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	34	48	mΩ	V _{GS} = -10V, I _D = -5A
			44	60		V _{GS} = -4.5V, I _D = -4A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1525	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	90	—	pF	
Reverse Transfer Capacitance	C _{riss}	—	70	—	pF	
Gate Resistance	R _g	—	16	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	14.5	—	nC	V _{DS} = -30V, I _D = -5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	30.6	—	nC	
Gate-Source Charge	Q _{gs}	—	4.9	—	nC	
Gate-Drain Charge	Q _{gd}	—	5.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.3	—	ns	
Turn-On Rise Time	t _R	—	15.4	—	ns	V _{GS} = -10V, V _{DS} = -30V, R _G = 3Ω, I _D = -5A
Turn-Off Delay Time	t _{D(OFF)}	—	79.2	—	ns	
Turn-Off Fall Time	t _F	—	45.3	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	15.2	—	ns	I _F = -5A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	9.3	—	nC	I _F = -5A, di/dt = -100A/µs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

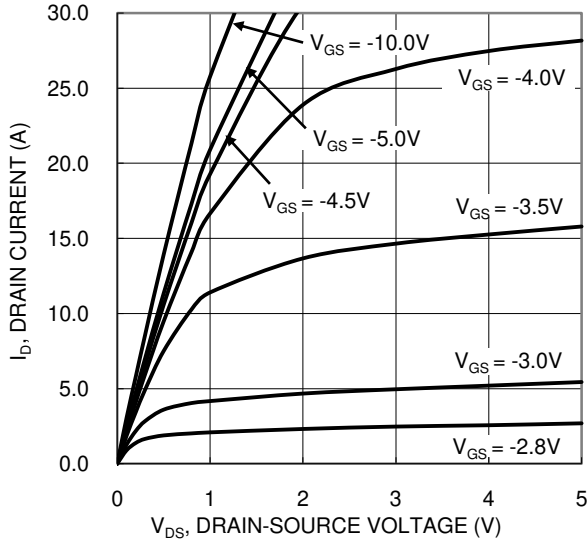


Figure 1. Typical Output Characteristic

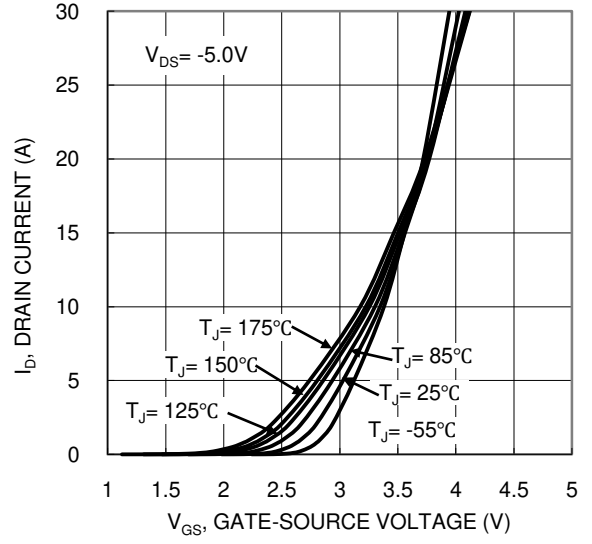


Figure 2. Typical Transfer Characteristic

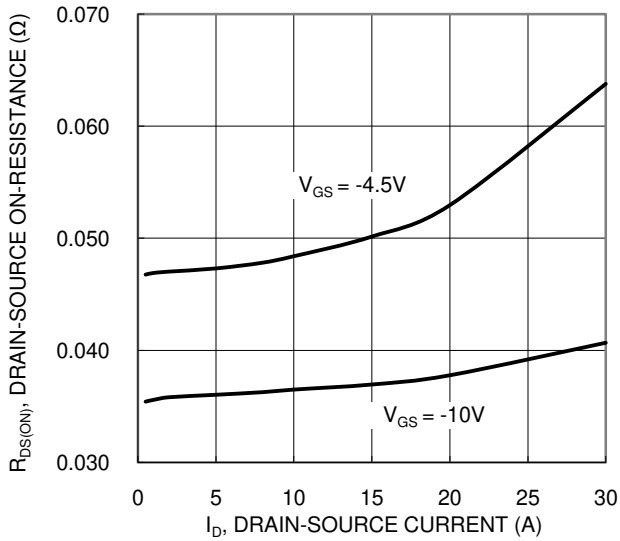


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

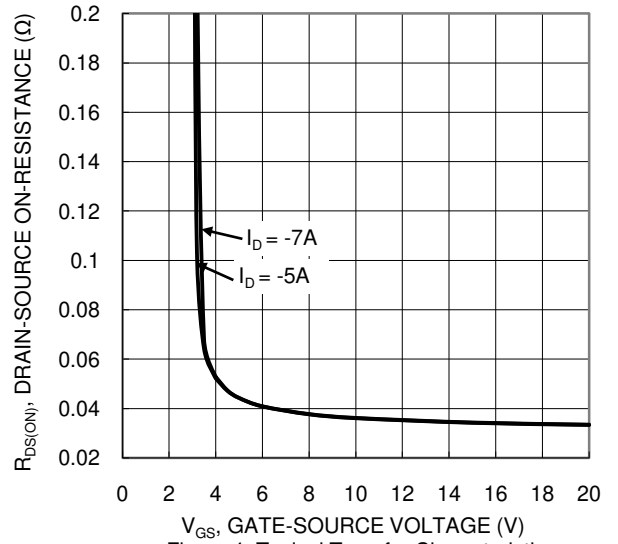


Figure 4. Typical Transfer Characteristic

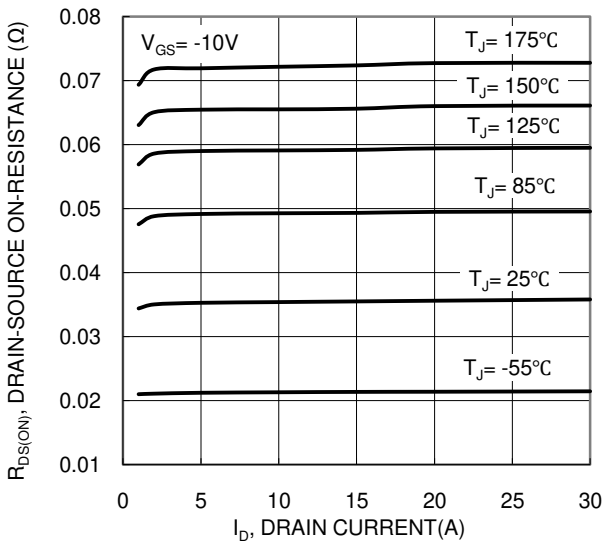


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

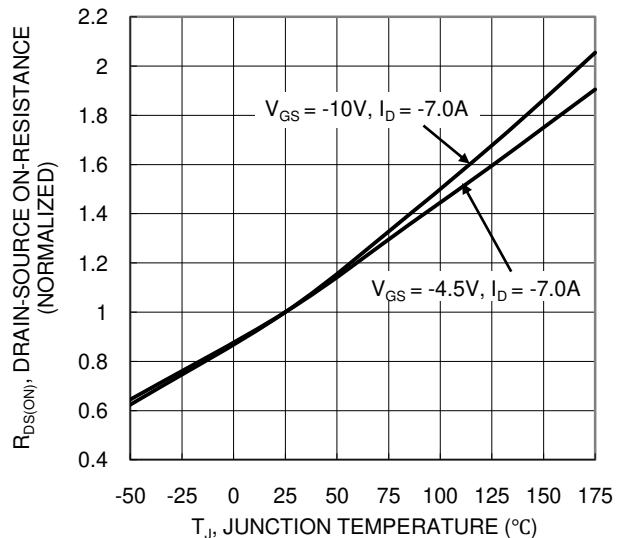
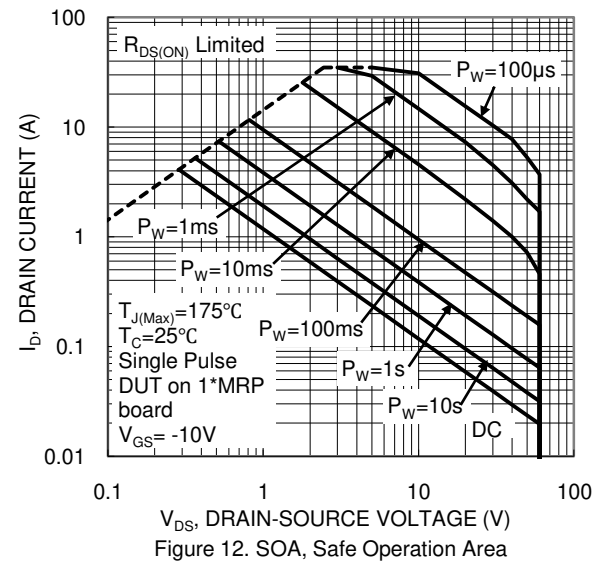
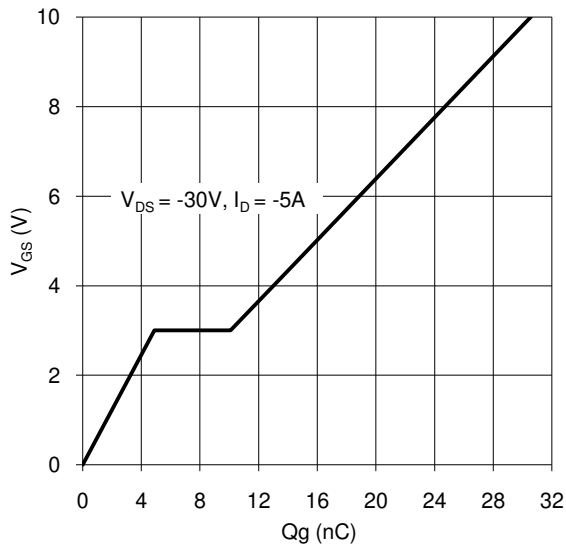
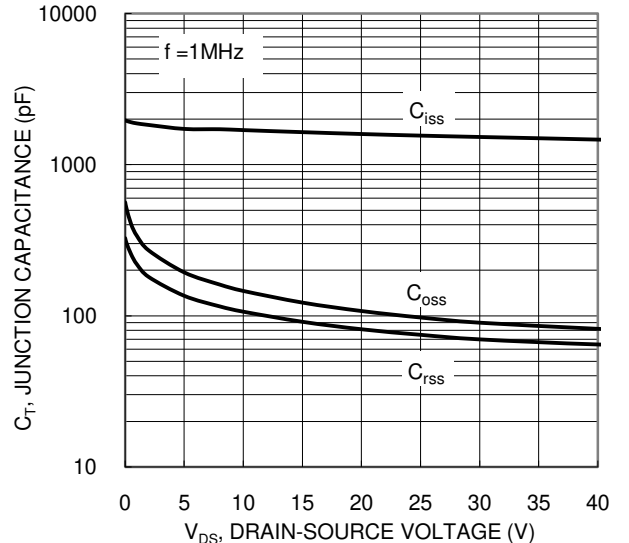
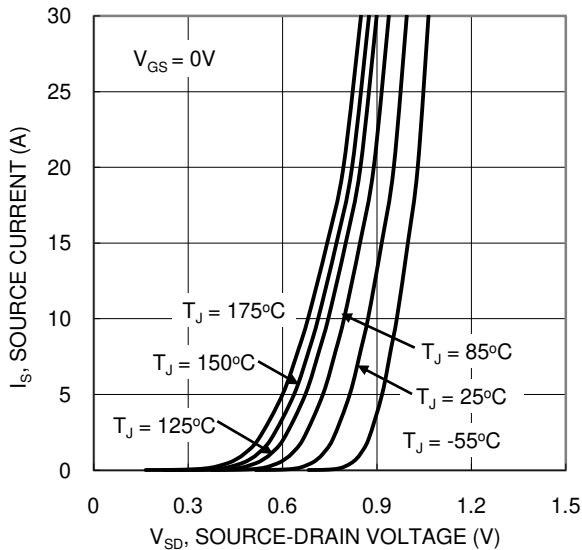
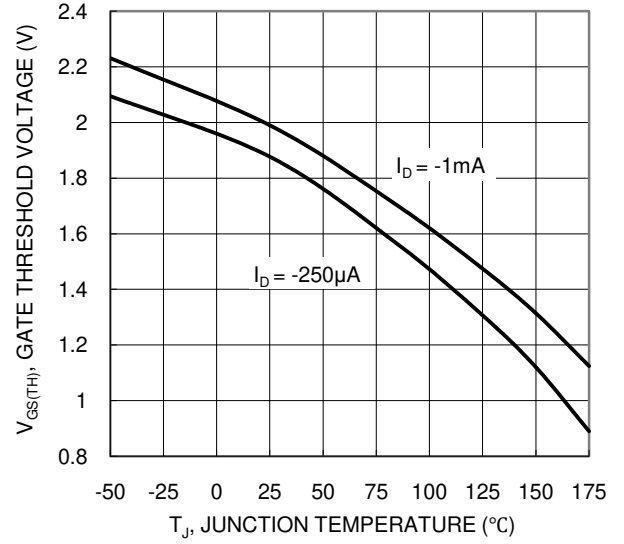
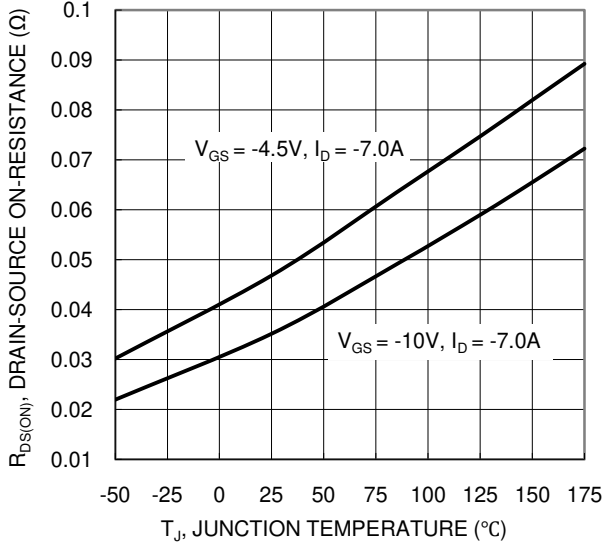


Figure 6. On-Resistance Variation with Temperature



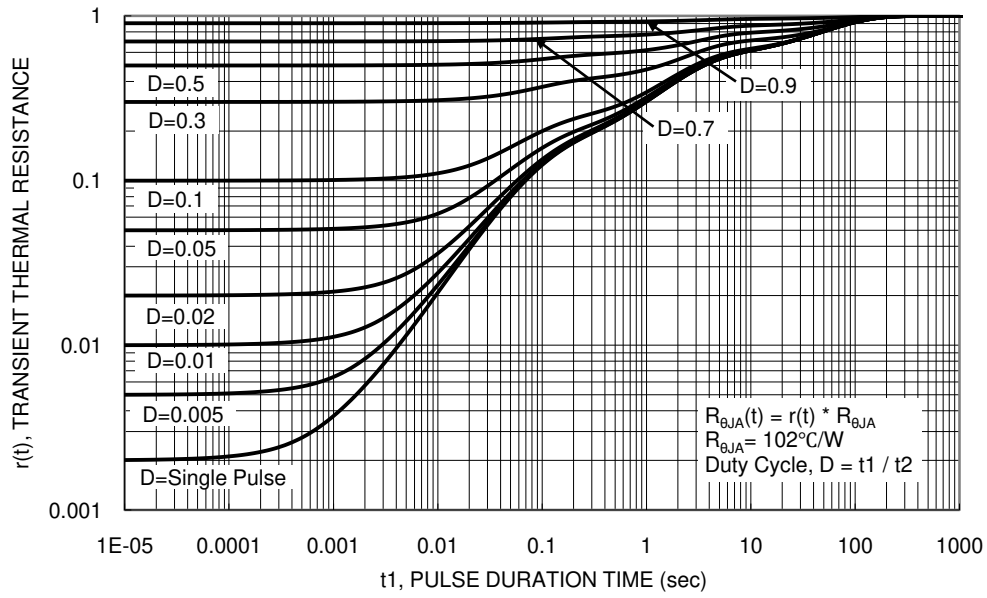
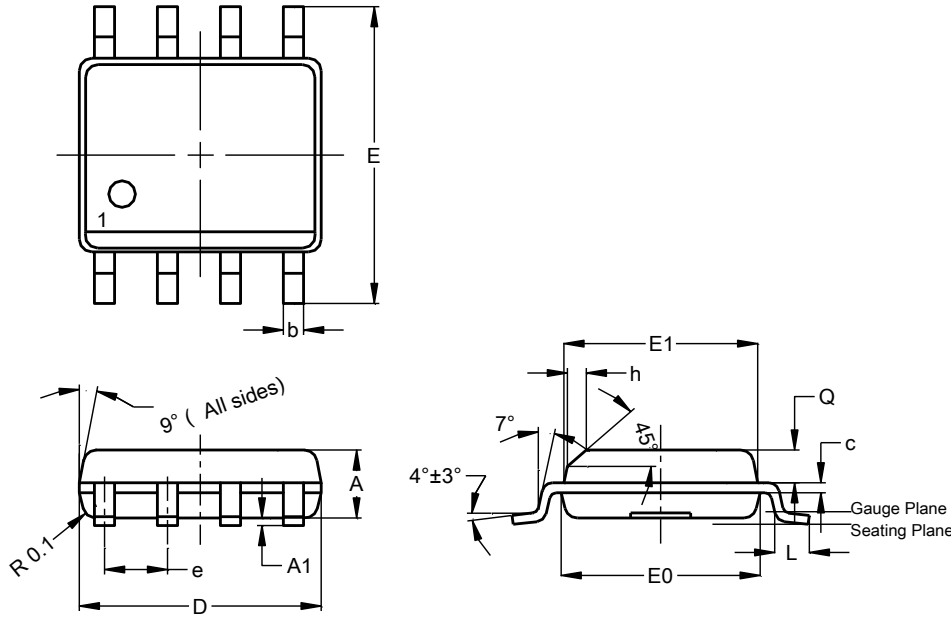


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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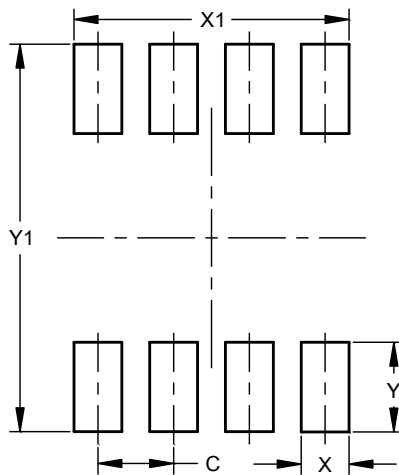


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Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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